

## HIGH EFFICIENCY FAST RECOVERY RECTIFIER DIODES

### MAIN PRODUCTS CHARACTERISTICS

$I_{F(AV)}$	20 A
$V_{RRM}$	200 V
$T_j$ (max)	150°C
$V_F$ (max)	0.85 V
$t_{rr}$ (max)	35 ns

### FEATURES

- Suited for SMPS
- Very low forward losses
- Negligible switching losses
- High surge current capability
- Insulated packages:  
ISOWATT220AC / TO-220FPAC:  
Insulation voltage = 2000 V DC  
Capacitance = 12 pF

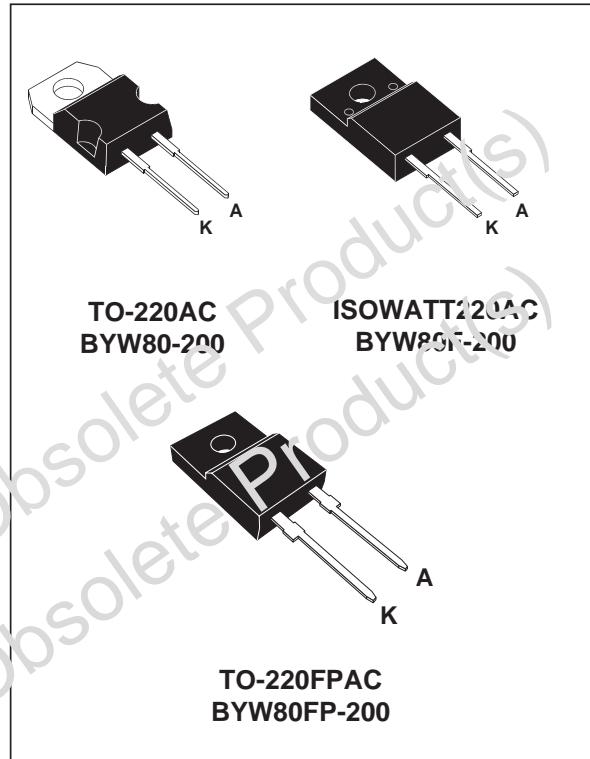
### DESCRIPTION

Single chip rectifier suited for Switch Mode Power Supplies and high frequency DC to DC converters.

Packaged in TO-220AC, ISOWATT220AC and TO-220FPAC this device is intended for use in low voltage, high frequency inverters, free wheeling and polarity protection applications.

### ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter			Value	Unit
$V_{RRM}$	Repetitive peak reverse voltage			200	V
$I_{F(RMS)}$	RMS forward current			20	A
$I_{F(AV)}$	$\delta = 0.5$	TO-220AC	$T_c=120^\circ\text{C}$	10	A
		ISOWATT220AC TO-220FPAC	$T_c=95^\circ\text{C}$	10	
$I_{FSM}$	Surge non repetitive forward current		$t_p=10\text{ms}$ sinusoidal	100	A
$T_{stg}$	Storage and junction temperature range			- 65 to + 150	°C
$T_j$	Maximum operating temperature range			+ 150	°C



## BYW80F/FP-200

### THERMAL RESISTANCE

Symbol	Parameter		Value	Unit
$R_{th} (j-c)$	Junction to case	TO-220AC	2.5	°C/W
		ISOWATT220AC / TO-220FPAC	4.7	

### ELECTRICAL CHARACTERISTICS STATIC CHARACTERISTICS

Symbol	Test Conditions		Min.	Typ.	Max.	Unit
$I_R$ *	$T_j = 25^\circ C$	$V_R = V_{RRM}$			10	$\mu A$
	$T_j = 100^\circ C$				1	mA
$V_F$ **	$T_j = 125^\circ C$	$I_F = 7 A$			0.85	V
	$T_j = 125^\circ C$	$I_F = 15 A$			1.05	
	$T_j = 25^\circ C$	$I_F = 15 A$			1.15	

Pulse test : \*  $t_p = 5$  ms, duty cycle < 2 %

\*\*  $t_p = 380$   $\mu s$ , duty cycle < 2 %

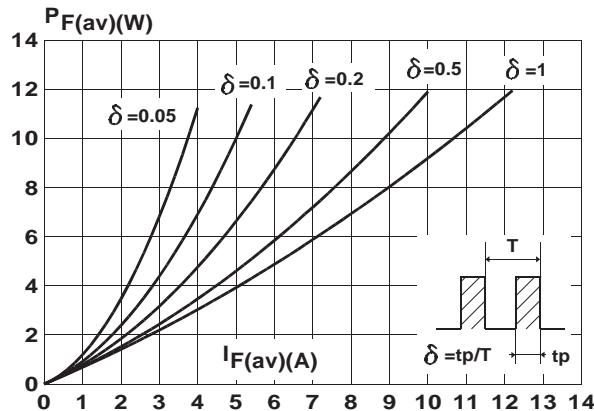
To evaluate the conduction losses use the following equation :

$$P = 0.65 \times I_{F(AV)} + 0.027 \times I_F^2(RMS)$$

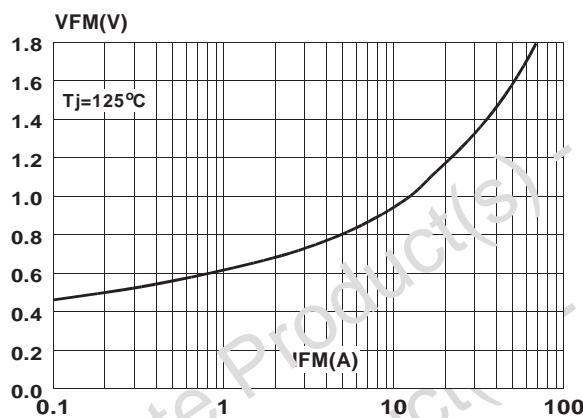
### RECOVERY CHARACTERISTICS

Symbol	Test Conditions		Min.	Typ.	Max.	Unit
$trr$	$T_j = 25^\circ C$	$I_F = 0.5A$	$I_{rr} = 0.25A$		25	ns
		$I_R = 1A$			35	
$tfr$	$T_j = 25^\circ C$	$I_F = 1A$ $V_R = 30V$	$dI_F/dt = -50A/\mu s$		15	ns
$V_{FP}$	$T_j = 25^\circ C$	$I_F = 1A$ $V_{FR} = 1.1 \times V_F$	$tr = 10$ ns		2	V

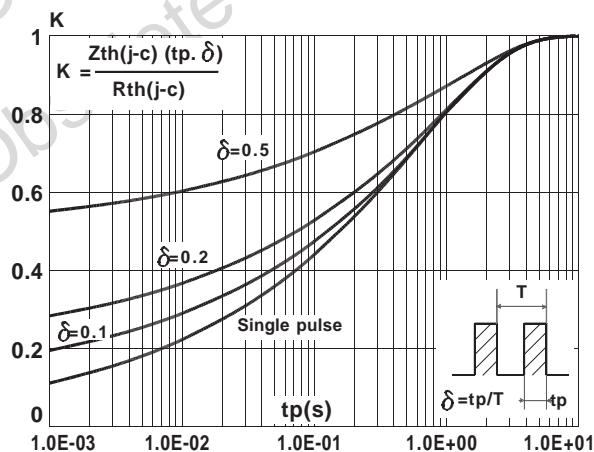
**Fig. 1:** Average forward power dissipation versus average forward current



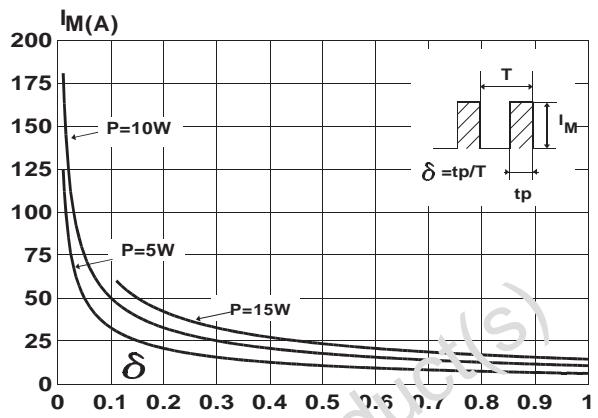
**Fig. 3:** Forward voltage drop versus forward current (maximum values)



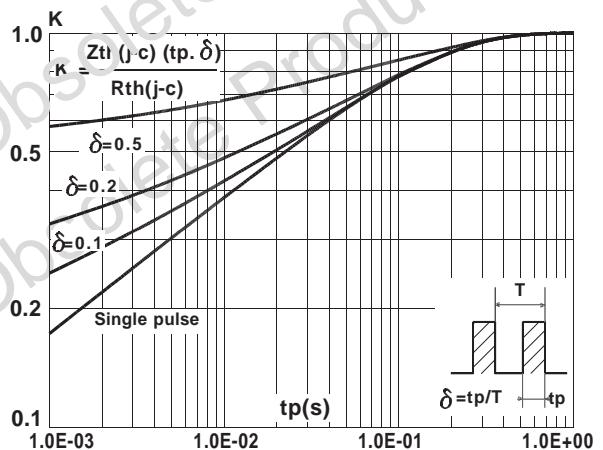
**Fig. 5:** Relative variation of thermal impedance junction to case versus pulse duration.  
(ISDWATT220AC / TO-220FPAC)



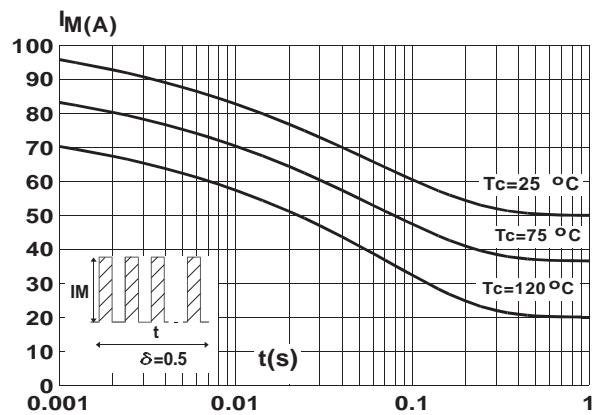
**Fig. 2:** Peak current versus form factor



**Fig. 4:** Relative variation of thermal impedance junction to case versus pulse duration (TO-220AC)

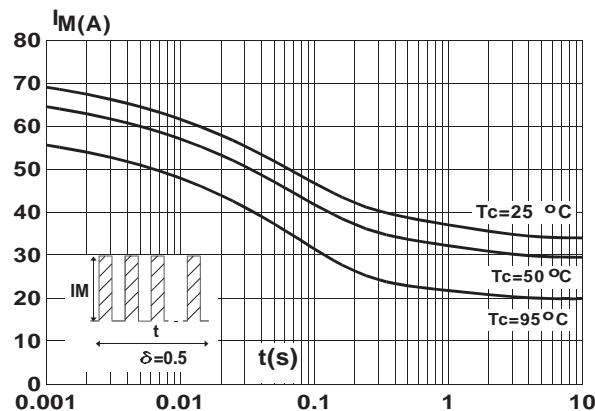


**Fig. 6:** Non repetitive surge peak forward current versus overload duration (TO-220AC)

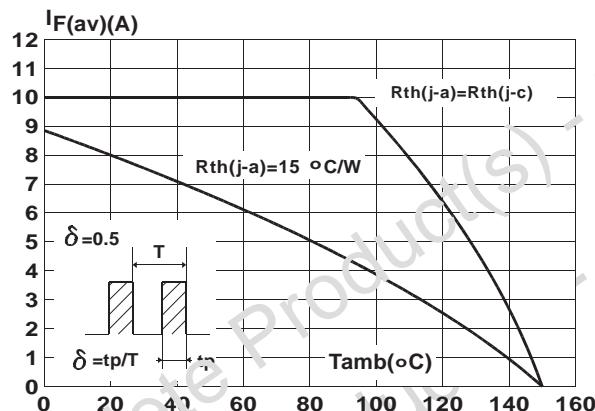


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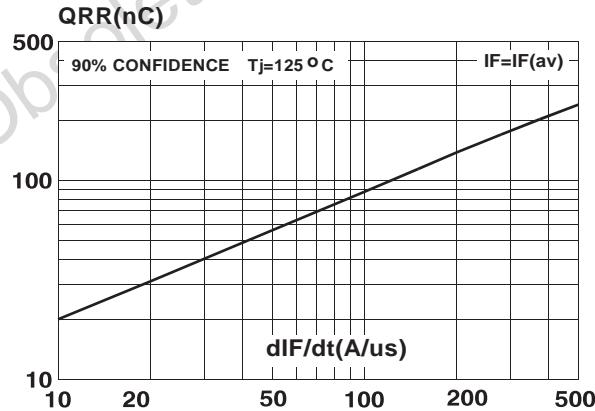
**Fig. 7:** Non repetitive surge peak forward current versus overload duration (ISOWATT220AC / TO-220FPAC)



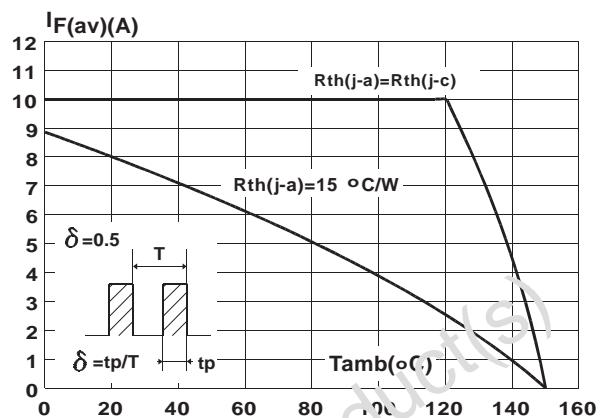
**Fig. 9:** Average current versus ambient temperature (duty cycle: 0.5) (ISOWATT220AC / TO-220FPAC)



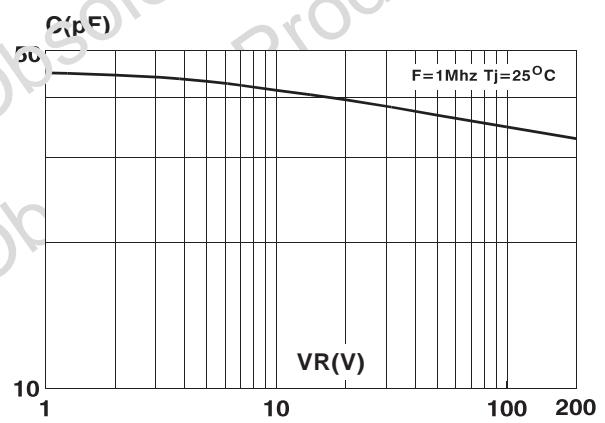
**Fig. 11:** Recovery charges versus  $dI_F/dt$ .



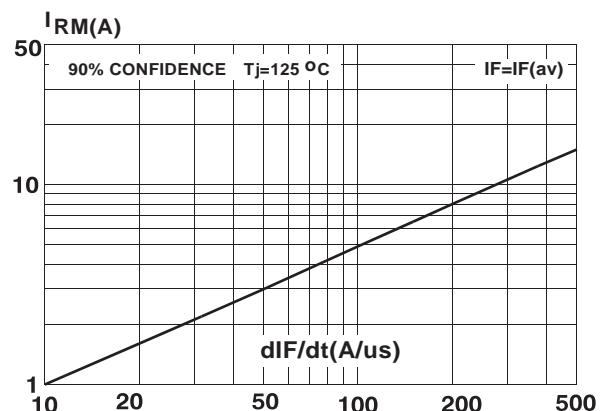
**Fig. 8:** Average current versus ambient temperature (duty cycle : 0.5) (TO-220AC)



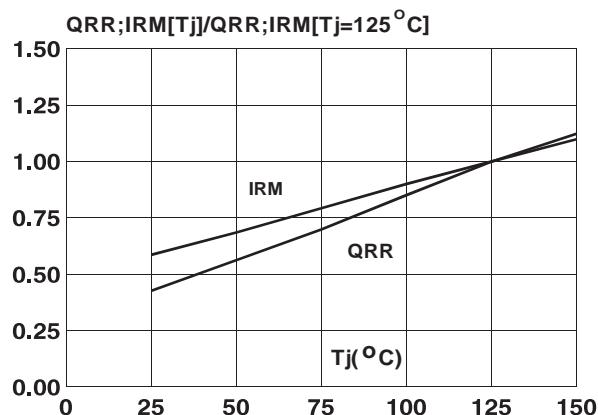
**Fig. 10:** Junction capacitance versus reverse voltage applied (Typical values)



**Fig. 12:** Peak reverse current versus  $dI_F/dt$ .



**Fig. 13:** Dynamic parameters versus junction temperature

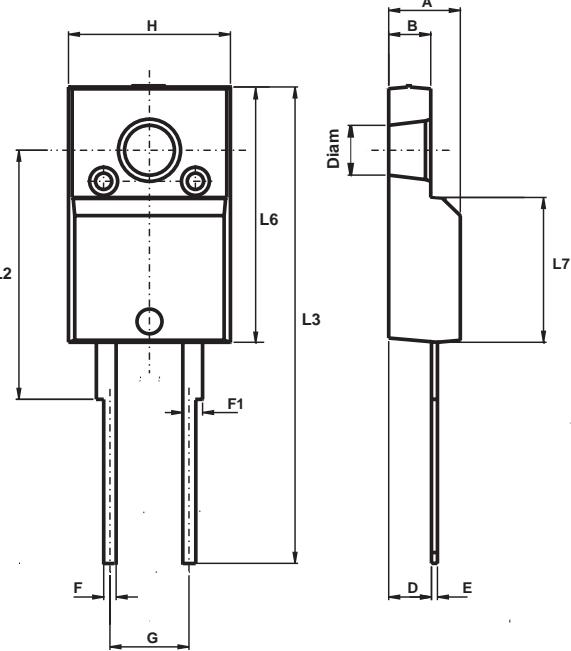


**PACKAGE MECHANICAL DATA**  
TO-220AC (JEDEC outline)

REF.	DIMENSIONS			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	4.40	4.60	0.173	0.181
C	1.23	1.32	0.048	0.051
D	2.40	2.72	0.094	0.107
E	0.49	0.70	0.019	0.027
F	0.61	0.88	0.024	0.034
F1	1.14	1.70	0.044	0.066
G	4.95	5.15	0.194	0.202
H2	10.00	10.40	0.393	0.409
L2	16.40 typ.		0.645 typ.	
L4	13.00	14.00	0.511	0.551
L5	2.65	2.95	0.104	0.116
L6	15.25	15.75	0.600	0.620
L7	6.20	6.60	0.244	0.259
L9	3.50	3.93	0.137	0.154
M	2.6 typ.		0.102 typ.	
Diam. I	3.75	3.85	0.147	0.151

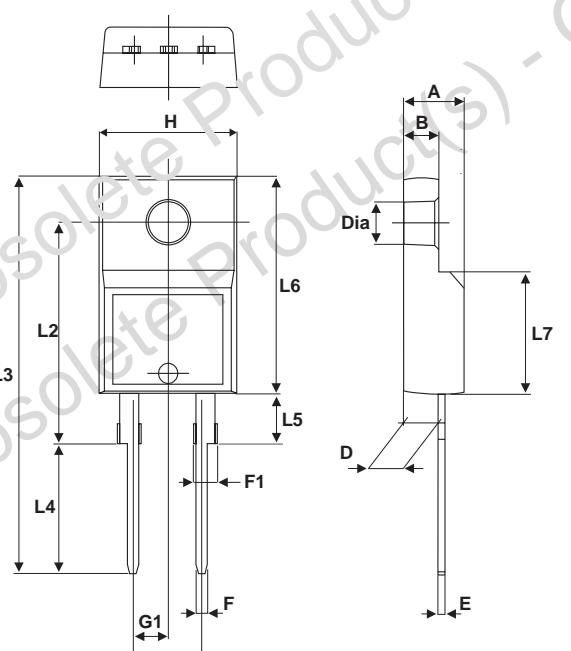
## BYW80F/FP-200

### PACKAGE MECHANICAL DATA ISOWATT220AC (JEDEC outline)



REF.	DIMENSIONS			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	4.40	4.60	0.173	0.181
B	2.50	2.70	0.098	0.106
D	2.40	2.75	0.094	0.108
E	0.40	0.70	0.016	0.028
F	0.75	1.00	0.030	0.039
F1	1.15	1.70	0.045	0.067
G	4.95	5.20	0.195	0.205
H	10.00	10.40	0.394	0.409
L2	16.00 typ.		0.63 typ.	
L3	28.60	30.60	1.125	1.205
L6	15.30	16.40	0.626	0.646
L7	9.00	9.30	0.354	0.366
Diam	3.00	3.20	0.118	0.126

### PACKAGE MECHANICAL DATA TO-220FPAC



REF.	DIMENSIONS			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	4.4	4.6	0.173	0.181
B	2.5	2.7	0.098	0.106
D	2.5	2.75	0.098	0.108
E	0.45	0.70	0.018	0.027
F	0.75	1	0.030	0.039
F1	1.15	1.70	0.045	0.067
G	4.95	5.20	0.195	0.205
G1	2.4	2.7	0.094	0.106
H	10	10.4	0.393	0.409
L2	16 Typ.		0.63 Typ.	
L3	28.6	30.6	1.126	1.205
L4	9.8	10.6	0.386	0.417
L5	2.9	3.6	0.114	0.142
L6	15.9	16.4	0.626	0.646
L7	9.00	9.30	0.354	0.366
Dia.	3.00	3.20	0.118	0.126

## **BYW80F/FP-200**

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Type	Marking	Package	Weight	Base Qty	Delivery mode
BYW80-200	BYW80-200	TO-220AC	2.3 g	50	Tube
BYW80F-200	BYW80F-200	ISOWATT220AC	2 g	50	Tube
BYW80FP-200	BYW80FP-200	TO-220FPAC	1.8 g	50	Tube

- Cooling method: by conduction (C)
- Recommended torque value (ISOWATT220AC, TO-220FPAC): 0.55 nm
- Maximum torque value (ISOWATT220AC, TO-220FPAC): 0.7 Nm
- Recommended torque value (TO-220AC): 0.8 Nm
- Maximum torque value (TO-220AC): 1.0 Nm
- Epoxy meets UL94, V0

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